

# GTL2010 Comparison Data

ASMC Shanghai  
vs.  
PSA Albuquerque

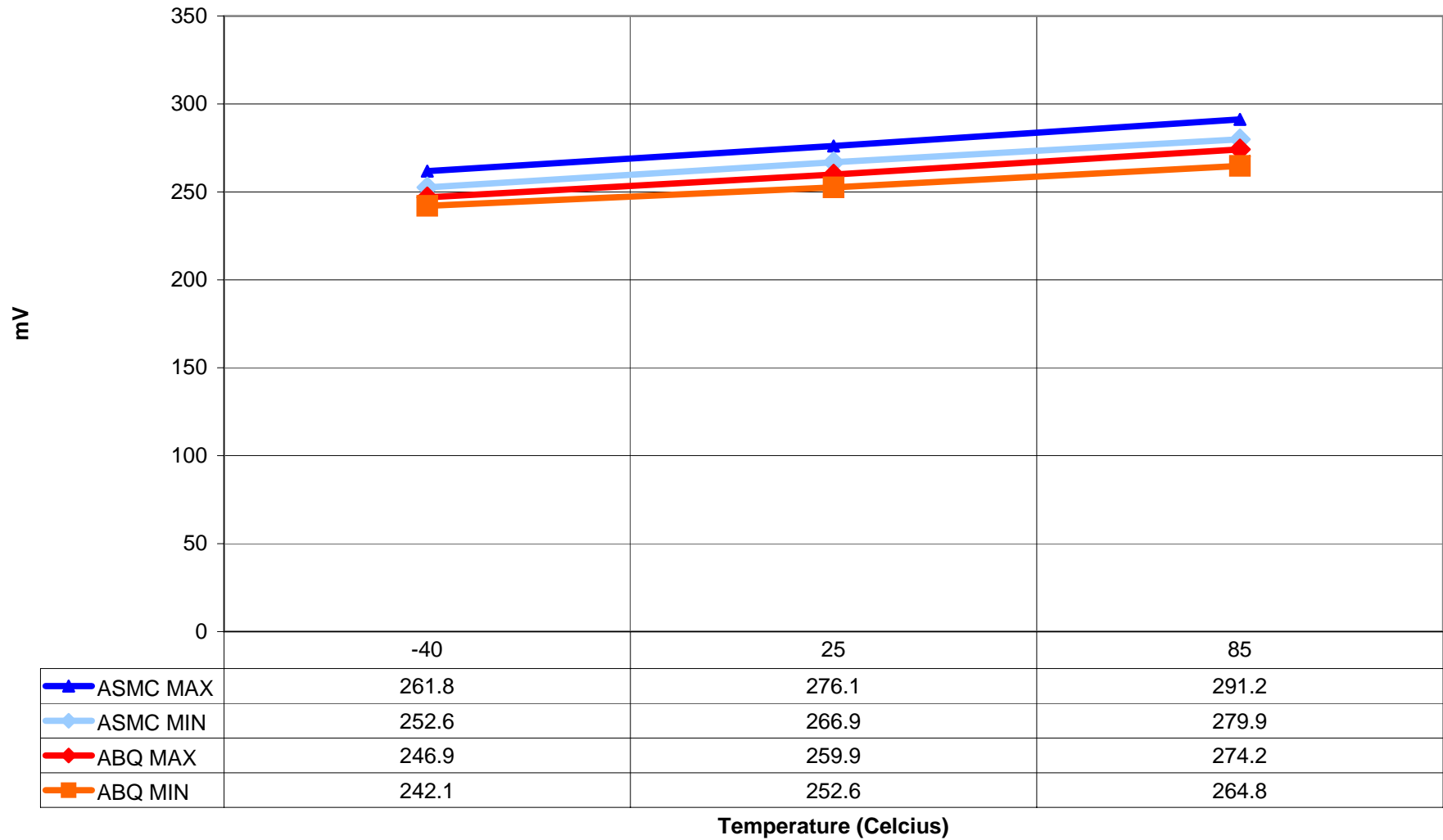
**PHILIPS**

## **GTL2010 History (ASMC Shanghai, China Fab)**

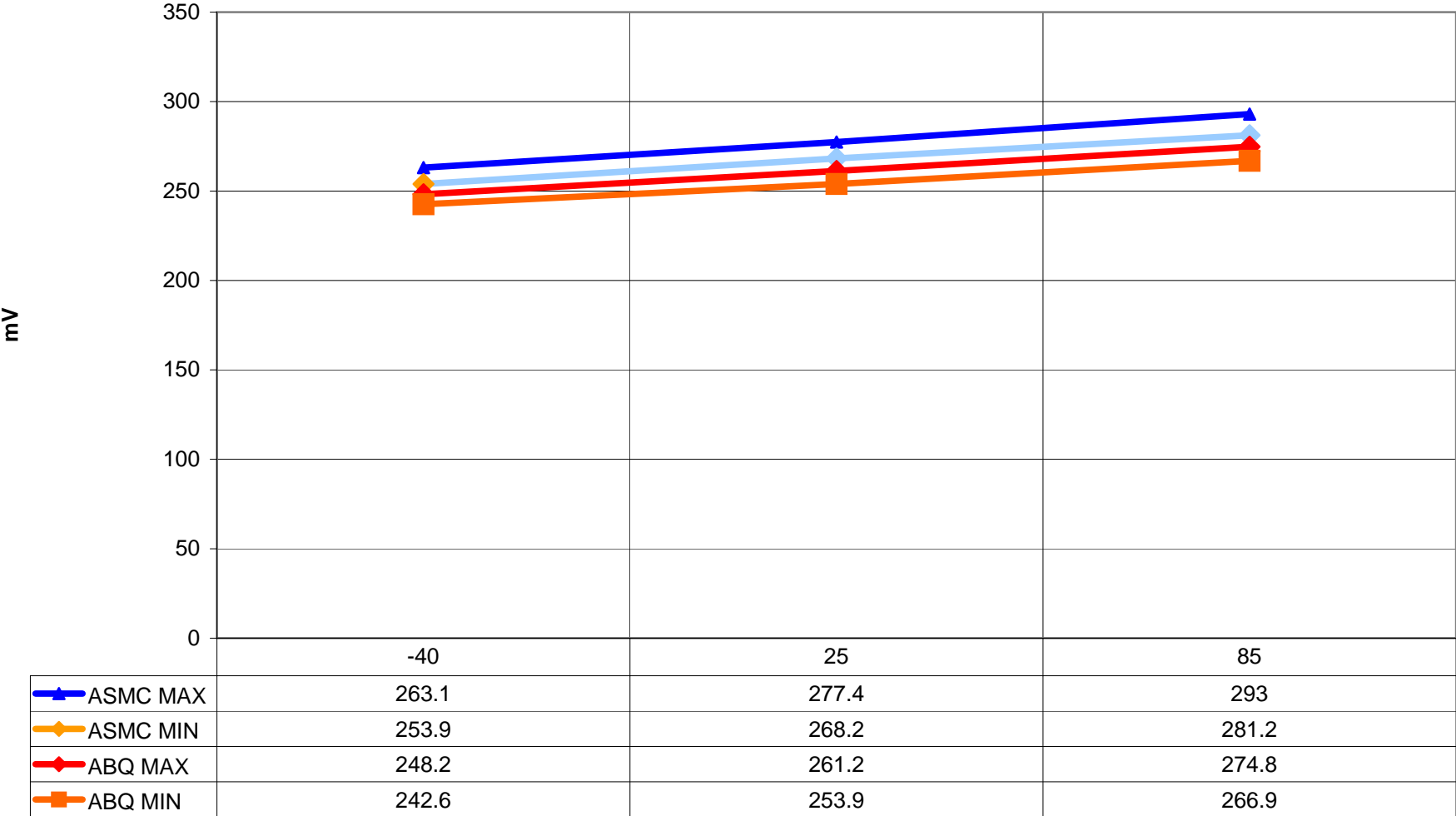
**July 2005**

The GTL2010 was originally designed using the QubicLP process in Albuquerque, New Mexico. After the closure of the Albuquerque facility in 2003, the QubicLP process was no longer available. The process was transferred to the ASMC Shanghai, China Fab and the original Albuquerque masks were used for the fabrication process.

GTL2010  
 $V_{OL} V_{DD}=3.0V V_{SN}=0.175V$



GTL2010  
 $V_{OL} V_{DD}=3.6V V_{SN}=0.175$

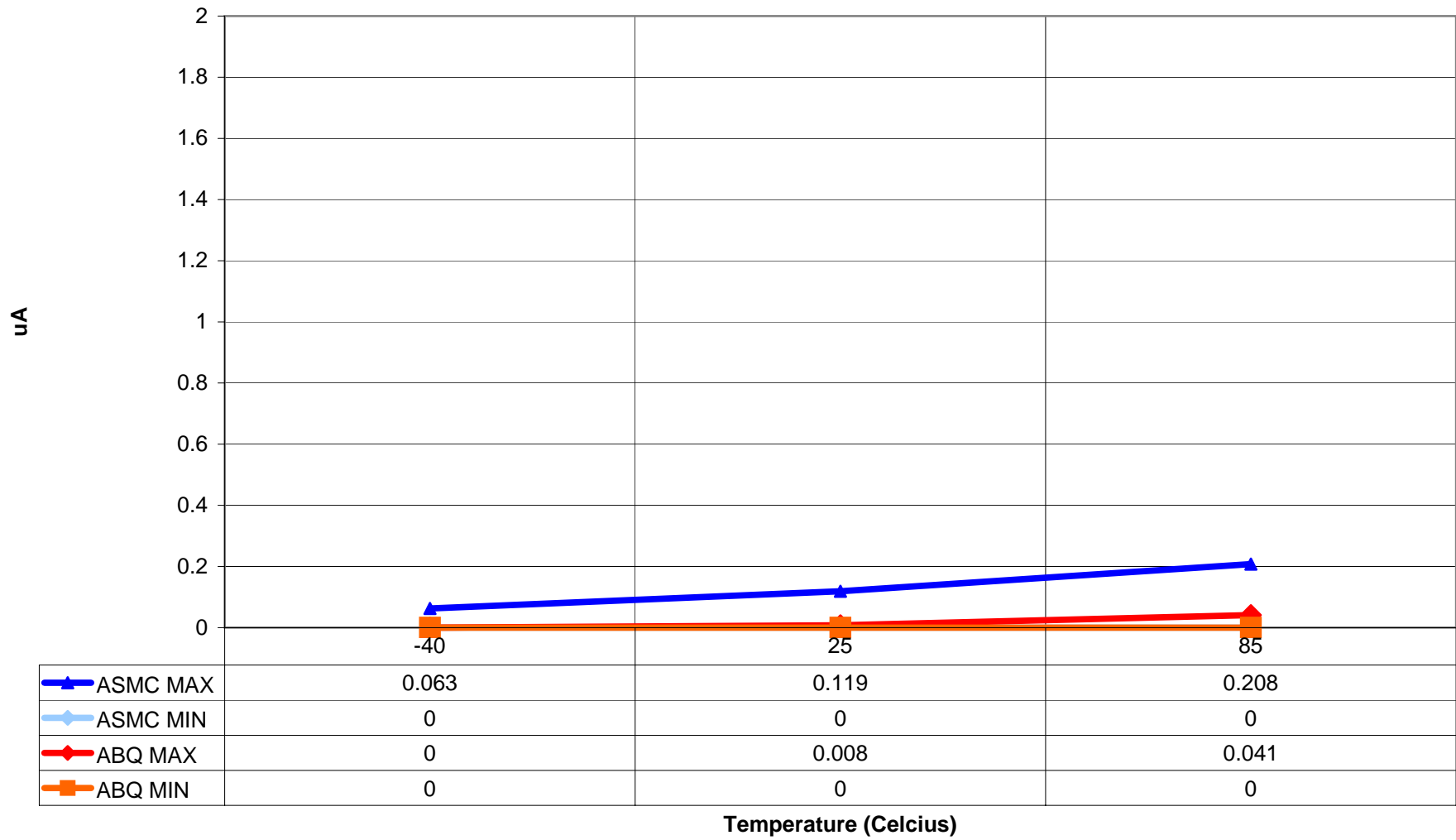


Temperature (Celcius)

GTL2010

$I_{IH}$

PHILIPS

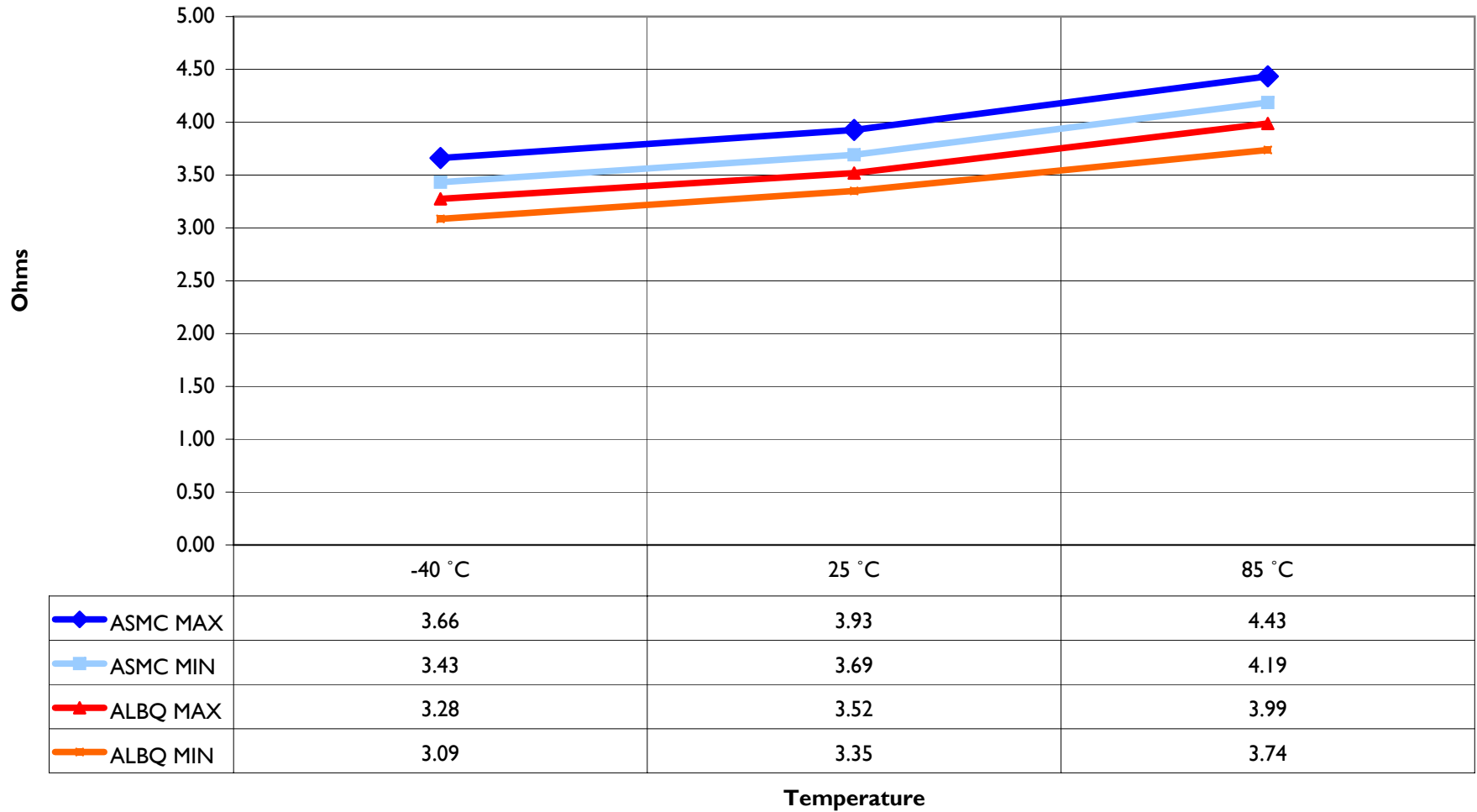


# PHILIPS

<b>GTL2010</b>					
ASMC			ALBQ		
CIO (OFF)					
MIN	6.00	pF	MIN	6.44	pF
MEAN	6.18	pF	MEAN	6.55	pF
MAX	6.40	pF	MAX	6.72	pF
CIO (ON)					
MIN	16.20	pF	MIN	16.79	pF
MEAN	16.50	pF	MEAN	17.05	pF
MAX	16.90	pF	MAX	17.48	pF
CI (GREF)					
MIN	54.30	pF	MIN	55.32	pF
MEAN	54.40	pF	MEAN	55.44	pF
MAX	54.50	pF	MAX	55.65	pF

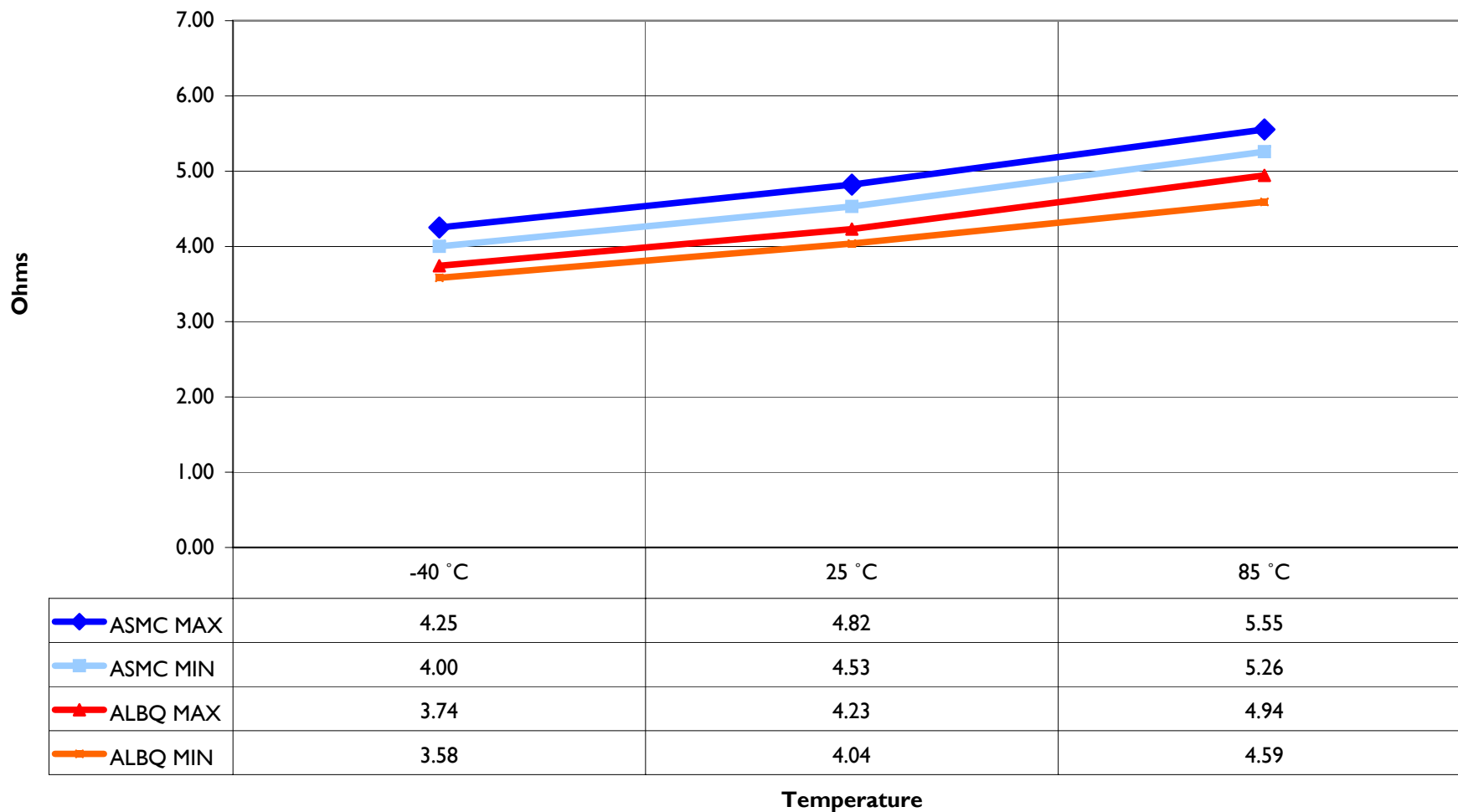
# GTL 2010 R<sub>ON</sub> 64mA

V<sub>I</sub> = 0.0V V<sub>GREF</sub> = 4.5V



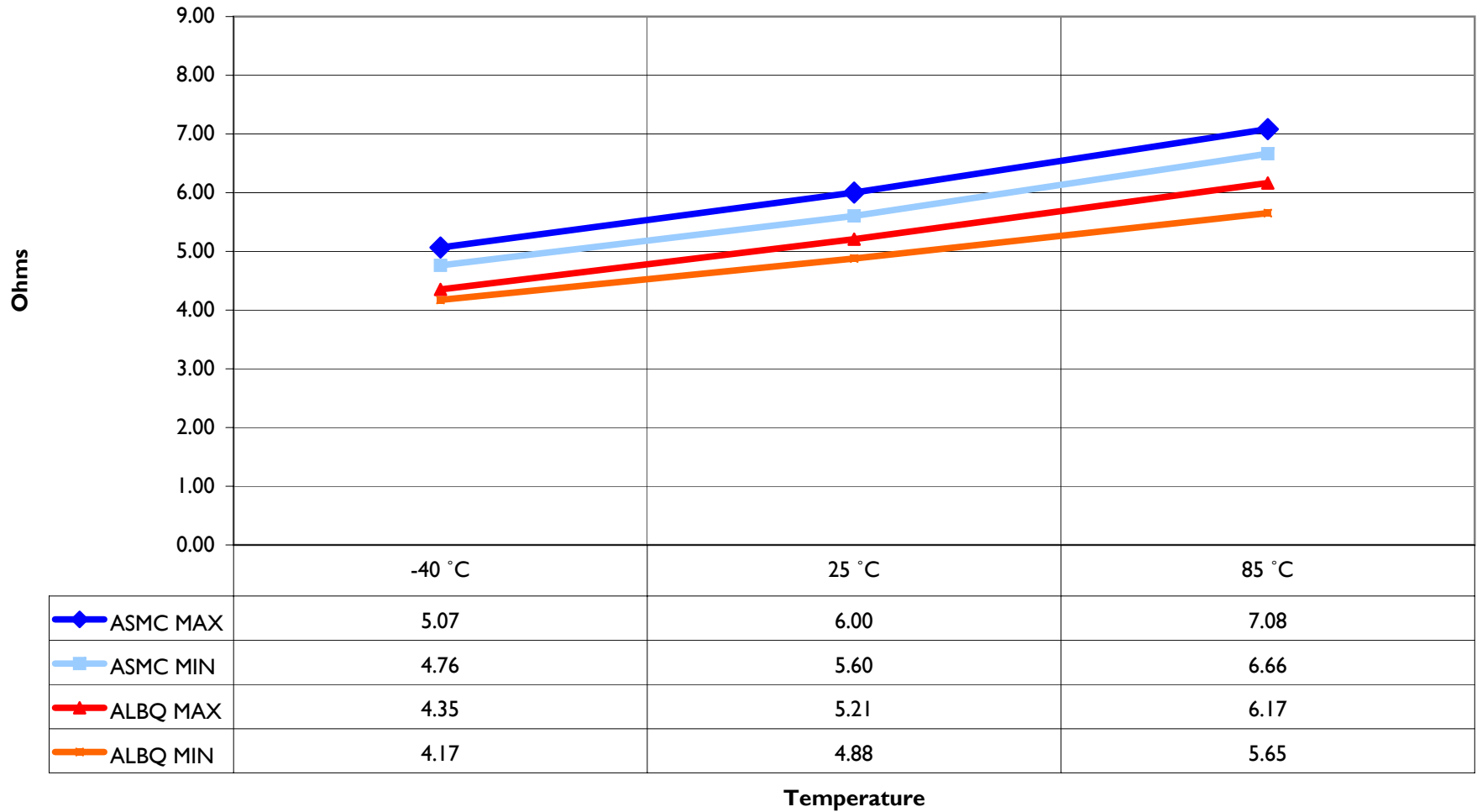
# GTL 2010 R<sub>ON</sub> 64mA

V<sub>I</sub> = 0.0V V<sub>GREF</sub> = 3.0V



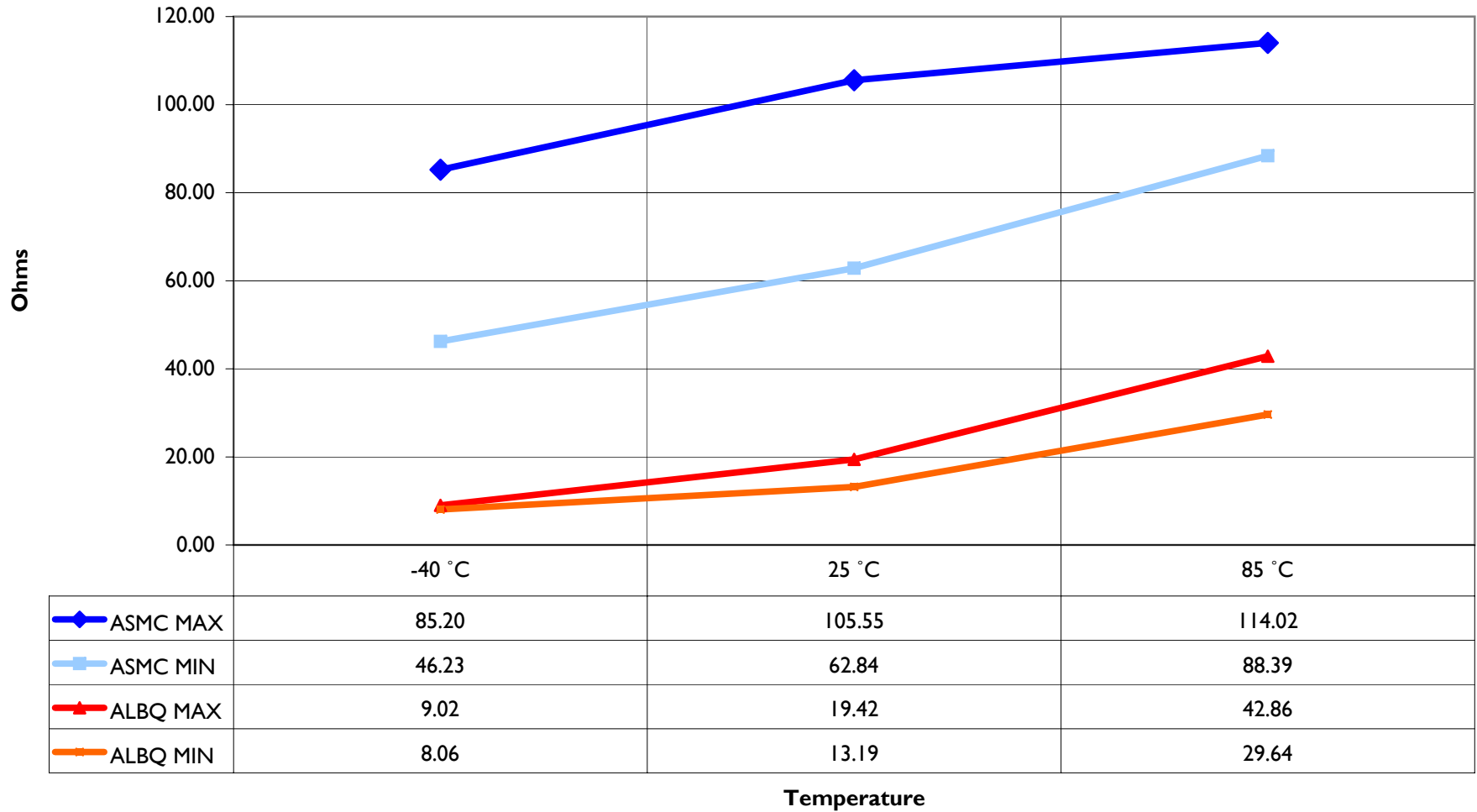
# GTL 2010 R<sub>ON</sub> 64mA

V<sub>I</sub> = 0.0V V<sub>GREF</sub> = 2.3V



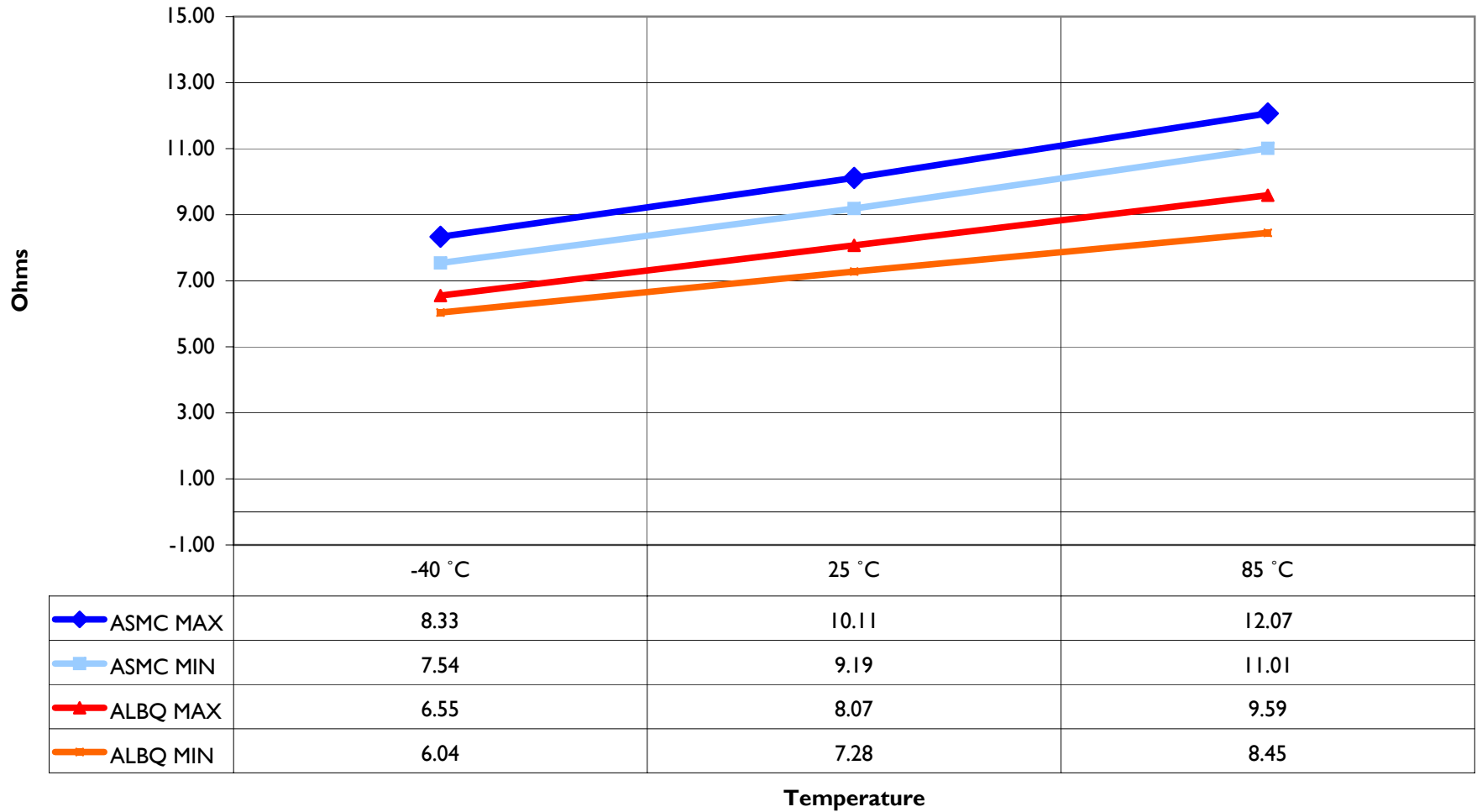
# GTL 2010 R<sub>ON</sub> 64mA

V<sub>I</sub> = 0.0V V<sub>GREF</sub> = 1.5V



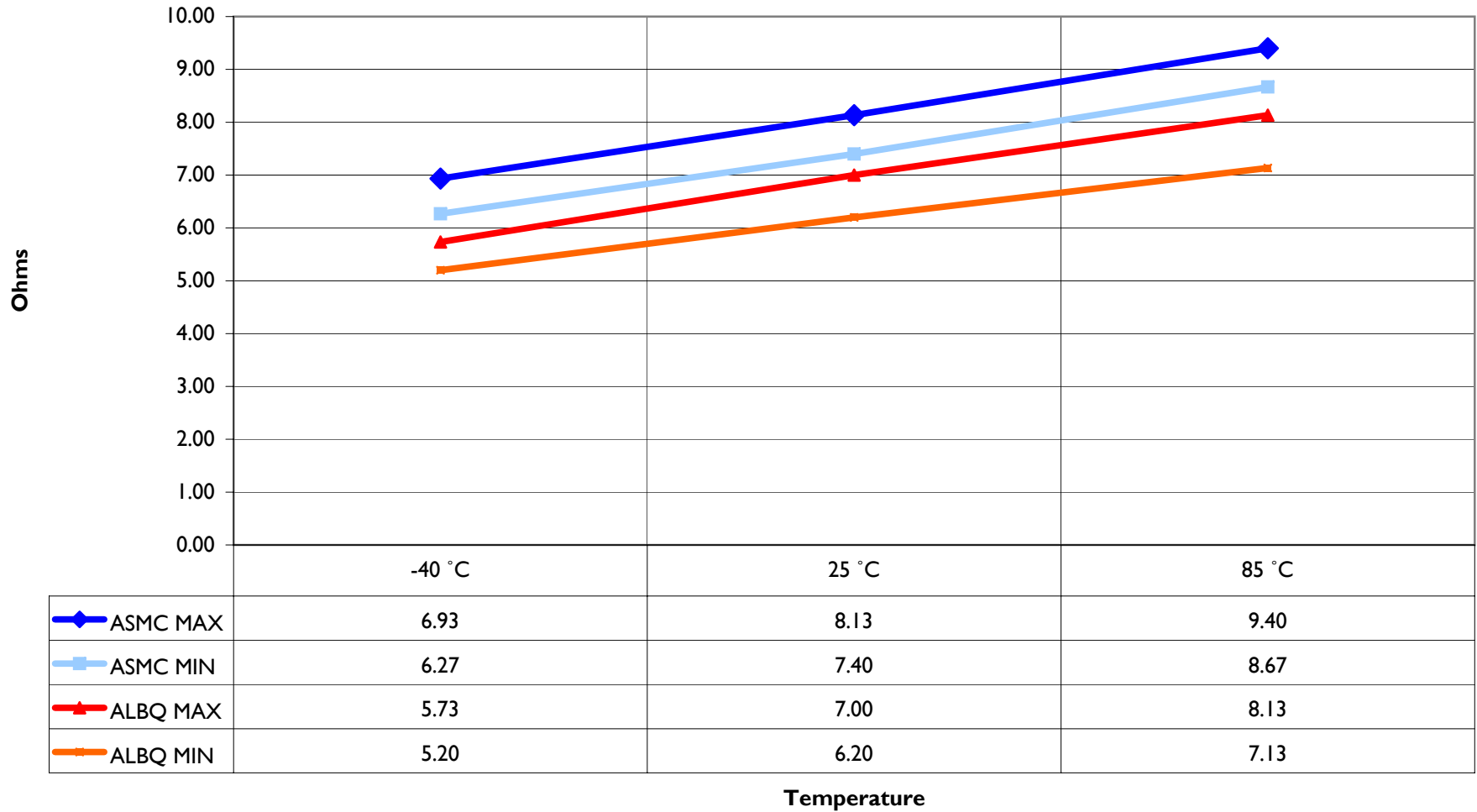
# GTL 2010 R<sub>ON</sub> 30mA

V<sub>I</sub> = 0.0V V<sub>GREF</sub> = 1.5V



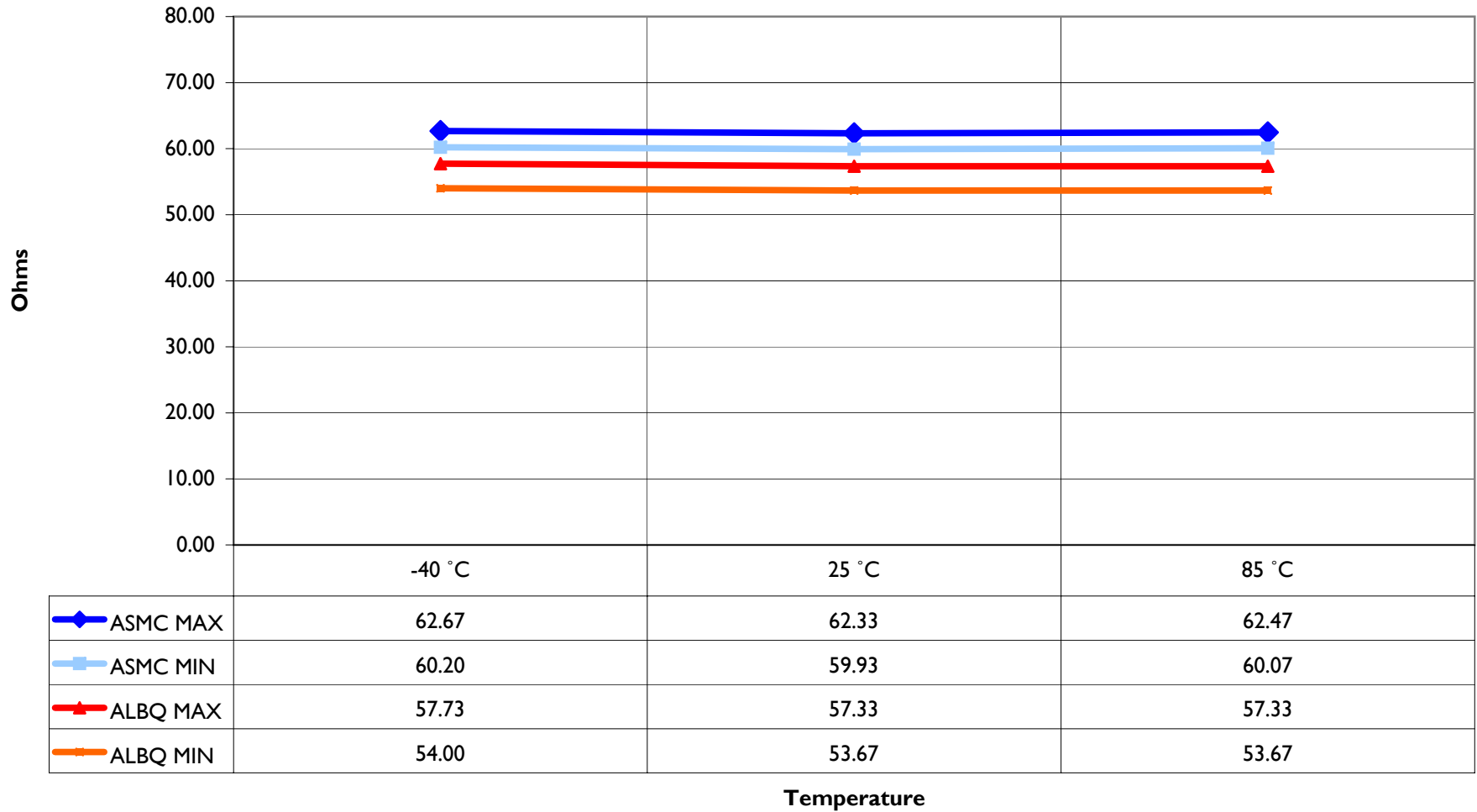
# GTL 2010 R<sub>ON</sub> 15mA

V<sub>I</sub> = 2.4V V<sub>GREF</sub> = 4.5V



# GTL 2010 R<sub>ON</sub> 15mA

V<sub>I</sub> = 2.4V V<sub>GREF</sub> = 3.0V



# GTL 2010 R<sub>ON</sub> 15mA

V<sub>I</sub> = 1.7V V<sub>GREF</sub> = 2.3V

